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4M High Speed SRAM (512-kword × 8-bit)

REJ03C0111-0200 Rev. 2.00 Dec.1.2008

### **Description**

The R1RW0408D is a 4-Mbit high speed static RAM organized 512-kword  $\times$  8-bit. It has realized high speed access time by employing CMOS process (6-transistor memory cell) and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. The R1RW0408D is packaged in 400-mil 36-pin SOJ for high density surface mounting.

#### **Features**

Single supply: 3.3 V ± 0.3 V
Access time: 10 ns /12 ns (max)

• Completely static memory

- No clock or timing strobe required

• Equal access and cycle times

• Directly TTL compatible

— All inputs and outputs

• Operating current: 115mA/100mA (max)

• TTL standby current: 40 mA (max)

• CMOS standby current: 5 mA (max)

: 0.8 mA (max) (L-version)

• Data retention current: 0.4 mA (max) (L-version)

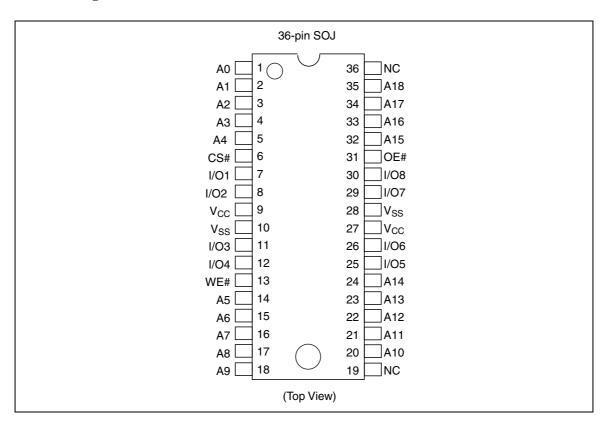
Data retention voltage: 2 V (min) (L-version)

• Center V<sub>CC</sub> and V<sub>SS</sub> type pin out

# **Ordering Information**

Type No.	Access time	Package
R1RW0408DGE-0PR	10 ns	
R1RW0408DGE-2PR	12 ns	400-mil 36-pin plastic SOJ (36P0K)
R1RW0408DGE-2LR	12 ns	

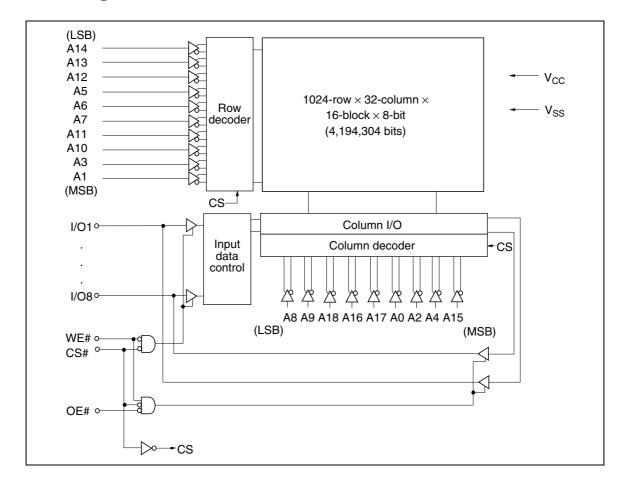
# **Pin Arrangement**



# **Pin Description**

Pin name	Function
A0 to A18	Address input
I/O1 to I/O8	Data input/output
CS#	Chip select
OE#	Output enable
WE#	Write enable
V <sub>cc</sub> V <sub>ss</sub>	Power supply
V <sub>SS</sub>	Ground
NC	No connection

# **Block Diagram**



# **Operation Table**

CS#	OE#	WE#	Mode	V <sub>CC</sub> current	I/O	Ref. cycle
Н	×	×	Standby	I <sub>SB</sub> , I <sub>SB1</sub>	High-Z	_
L	Н	Н	Output disable	I <sub>CC</sub>	High-Z	_
L	L	Н	Read	I <sub>CC</sub>	D <sub>OUT</sub>	Read cycle (1) to (3)
L	Н	L	Write	I <sub>CC</sub>	D <sub>IN</sub>	Write cycle (1)
L	L	L	Write	I <sub>CC</sub>	D <sub>IN</sub>	Write cycle (2)

Note: H:  $V_{IH}$ , L:  $V_{IL}$ ,  $\times$ :  $V_{IH}$  or  $V_{IL}$ 

## **Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Supply voltage relative to V <sub>SS</sub>	V <sub>CC</sub>	-0.5 to +4.6	V
Voltage on any pin relative to V <sub>SS</sub>	V <sub>T</sub>	$-0.5^{*1}$ to $V_{CC} + 0.5^{*2}$	V
Power dissipation	P <sub>T</sub>	1.0	W
Operating temperature	Topr	0 to +70	°C
Storage temperature	Tstg	-55 to +125	°C
Storage temperature under bias	Tbias	-10 to +85	°C

Notes: 1.  $V_T$  (min) = -2.0 V for pulse width (under shoot)  $\leq$  6 ns.

2.  $V_T$  (max) =  $V_{CC}$  + 2.0 V for pulse width (over shoot)  $\leq$  6 ns.

### **Recommended DC Operating Conditions**

 $(Ta = 0 \text{ to } +70^{\circ}C)$ 

Parameter	Symbol	Min	Тур	Max	Unit
Supply voltage	V <sub>CC</sub> *3	3.0	3.3	3.6	V
	V <sub>SS</sub> * <sup>4</sup>	0	0	0	V
Input voltage	V <sub>IH</sub>	2.0	_	V <sub>CC</sub> + 0.5* <sup>2</sup>	V
	V <sub>IL</sub>	-0.5* <sup>1</sup>	_	0.8	V

Notes: 1.  $V_{IL}$  (min) = -2.0 V for pulse width (under shoot)  $\leq$  6 ns.

- 2.  $V_{IH}$  (max) =  $V_{CC}$  + 2.0 V for pulse width (over shoot)  $\leq$  6 ns.
- 3. The supply voltage with all  $V_{\text{CC}}$  pins must be on the same level.
- 4. The supply voltage with all  $\ensuremath{V_{\text{SS}}}$  pins must be on the same level.

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### **DC** Characteristics

(Ta = 0 to +70°C,  $V_{CC}$  = 3.3 V  $\pm$  0.3 V,  $V_{SS}$  = 0 V)

Parameter		Symbo	ol Min	Max	Unit	Test conditions	
Input leakage current		II <sub>LI</sub> I	_	2	μΑ	$V_{IN} = V_{SS}$ to $V_{CC}$	
Output leakage current		II <sub>LO</sub> I	_	2	μΑ	$V_{IN} = V_{SS}$ to $V_{CC}$	
Operation power supply	10ns cycle	I <sub>CC</sub>	_	115	mA	Min cycle  — CS# = V <sub>II</sub> , I <sub>OUT</sub> = 0 mA	
current	12ns cycle	I <sub>CC</sub>	_	100	mA	Other inputs = $V_{IH}/V_{IL}$	
Standby power supply current		I <sub>SB</sub>	_	40	mA	Min cycle $CS\# = V_{IH}$ , $Other inputs = V_{IH}/V_{IL}$	
		I <sub>SB1</sub>		5	mA	$ f = 0 \text{ MHz} $ $V_{CC} \ge CS\# \ge V_{CC} - 0.2 \text{ V}, $ $(1) 0 \text{ V} \le V_{IN} \le 0.2 \text{ V or} $ $(2) V_{CC} \ge V_{IN} \ge V_{CC} - 0.2 \text{ V} $	
			*1	0.8*1	mA	<del>_</del>	
Output voltage		V <sub>OL</sub>	_	0.4	V	I <sub>OL</sub> = 8 mA	
		V <sub>OH</sub>	2.4	_	V	I <sub>OH</sub> = -4 mA	

Note: 1. This characteristics is guaranteed only for L-version.

# Capacitance

 $(Ta = +25^{\circ}C, f = 1.0 \text{ MHz})$ 

Parameter	Symbol	Min	Max	Unit	Test conditions
Input capacitance*1	C <sub>IN</sub>	_	6	pF	V <sub>IN</sub> = 0 V
Input/output capacitance*1	C <sub>I/O</sub>	_	8	pF	$V_{I/O} = 0 V$

Note: 1. This parameter is sampled and not 100% tested.

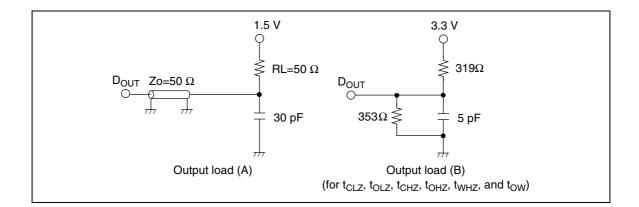
### **AC Characteristics**

(Ta = 0 to +70°C,  $V_{CC}$  = 3.3 V  $\pm$  0.3 V, unless otherwise noted.)

### **Test Conditions**

Input pulse levels: 3.0 V/0.0 VInput rise and fall time: 3 ns

Input and output timing reference levels: 1.5 VOutput load: See figures (Including scope and jig)



### Read Cycle

### R1RW0408D

		10ns Version		12ns Version			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read cycle time	t <sub>RC</sub>	10	_	12	_	ns	
Address access time	t <sub>AA</sub>	_	10	_	12	ns	
Chip select access time	t <sub>ACS</sub>	_	10	_	12	ns	
Output enable to output valid	t <sub>OE</sub>	_	5	_	6	ns	
Output hold from address change	t <sub>OH</sub>	3	_	3	_	ns	
Chip select to output in low-Z	t <sub>CLZ</sub>	3	_	3	_	ns	1
Output enable to output in low-Z	t <sub>OLZ</sub>	0	_	0	_	ns	1
Chip deselect to output in high-Z	t <sub>CHZ</sub>	_	5	_	6	ns	1
Output disable to output in high-Z	t <sub>OHZ</sub>	_	5		6	ns	1



#### Write Cycle

#### R1RW0408D

		10ns Version		12ns Version		_	
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	t <sub>WC</sub>	10	_	12	_	ns	
Address valid to end of write	t <sub>AW</sub>	7	_	8	_	ns	
Chip select to end of write	t <sub>CW</sub>	7	_	8	_	ns	9
Write pulse width	t <sub>WP</sub>	7	_	8	_	ns	8
Address setup time	t <sub>AS</sub>	0	_	0	_	ns	6
Write recovery time	t <sub>WR</sub>	0	_	0	_	ns	7
Data to write time overlap	t <sub>DW</sub>	5	_	6	_	ns	
Data hold from write time	t <sub>DH</sub>	0	_	0	_	ns	
Write disable to output in low-Z	t <sub>OW</sub>	3	_	3	_	ns	1
Output disable to output in high-Z	t <sub>OHZ</sub>	_	5	_	6	ns	1
Write enable to output in high-Z	t <sub>WHZ</sub>	_	5		6	ns	1

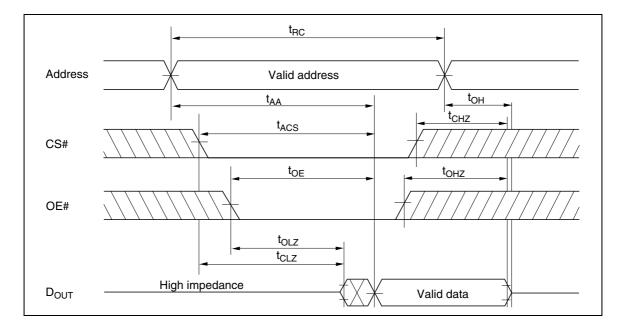
Notes: 1. Transition is measured ±200 mV from steady voltage with output load (B). This parameter is sampled and not 100% tested.

- 2. Address should be valid prior to or coincident with CS# transition low.
- 3. WE# and/or CS# must be high during address transition time.
- 4. If CS# and OE# are low during this period, I/O pins are in the output state. Then, the data input signals of opposite phase to the outputs must not be applied to them.
- 5. If the CS# low transition occurs simultaneously with the WE# low transition or after the WE# transition, output remains a high impedance state.
- 6. t<sub>AS</sub> is measured from the latest address transition to the later of CS# or WE# going low.
- 7.  $t_{\text{WR}}$  is measured from the earlier of CS# or WE# going high to the first address transition.
- 8. A write occurs during the overlap of a low CS# and a low WE#. A write begins at the latest transition among CS# going low and WE# going low. A write ends at the earliest transition among CS# going high and WE# going high. twp is measured from the beginning of write to the end of write.
- 9.  $t_{CW}$  is measured from the later of CS# going low to the end of write.

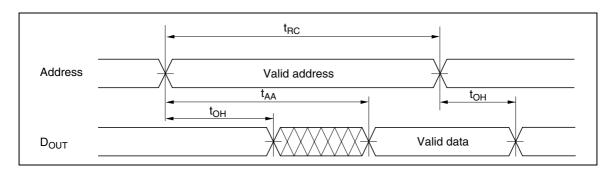


# **Timing Waveforms**

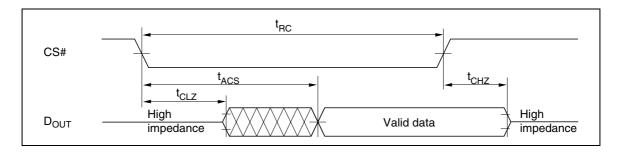
# Read Timing Waveform (1) (WE# = $V_{IH}$ )



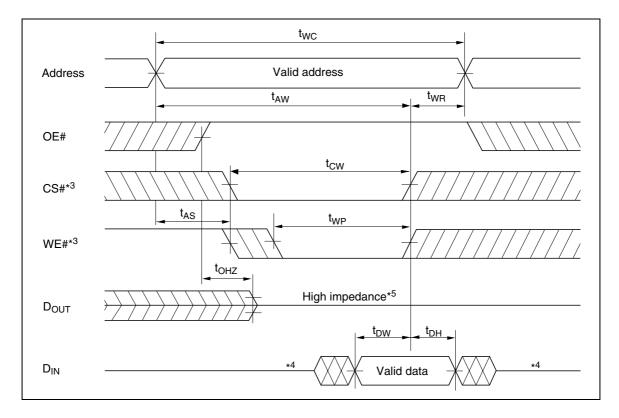
# Read Timing Waveform (2) (WE# = $V_{IH}$ , CS# = $V_{IL}$ , OE# = $V_{IL}$ )



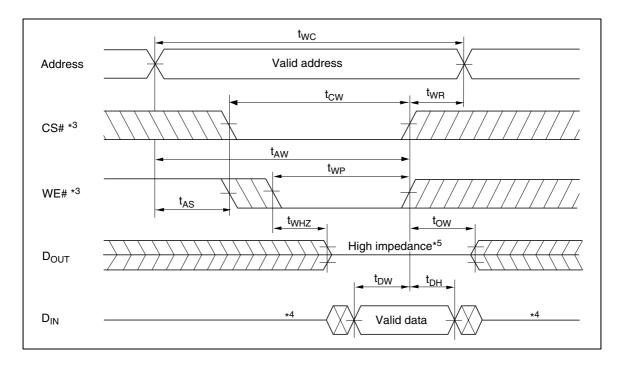
Read Timing Waveform (3) (WE# =  $V_{IH}$ , CS# =  $V_{IL}$ , OE# =  $V_{IL}$ )\* $^2$ 



# Write Timing Waveform (1) (WE# Controlled)



# Write Timing Waveform (2) (CS# Controlled)



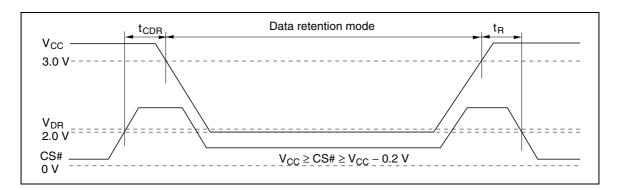
# Low $V_{CC}$ Data Retention Characteristics

 $(Ta = 0 \text{ to } +70^{\circ}\text{C})$ 

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Max	Unit	Test conditions
V <sub>CC</sub> for data retention	$V_{DR}$	2.0	_	V	$\begin{split} V_{CC} &\geq CS\# \geq V_{CC} - 0.2 \text{ V} \\ (1) & 0 \text{ V} \leq V_{IN} \leq 0.2 \text{ V or} \\ (2) & V_{CC} \geq V_{IN} \geq V_{CC} - 0.2 \text{ V} \end{split}$
Data retention current	I <sub>CCDR</sub>	_	400	μА	$V_{CC} = 3 \text{ V}, V_{CC} \ge \text{CS\#} \ge V_{CC} - 0.2 \text{ V}$ (1) $0 \text{ V} \le V_{IN} \le 0.2 \text{ V}$ or (2) $V_{CC} \ge V_{IN} \ge V_{CC} - 0.2 \text{ V}$
Chip deselect to data retention time	t <sub>CDR</sub>	0	_	ns	See retention waveform
Operation recovery time	t <sub>R</sub>	5	_	ms	

# Low $V_{\text{CC}}$ Data Retention Timing Waveform



# **Revision History**

# R1RW0408D Series Data Sheet

Rev.	Date	Conte	ontents of Modification					
		Page	Description					
0.01	Sep. 30, 2003	_	Initial issue					
1.00	Mar.12.2004	_	Deletion of Preliminary					
2.00	Dec.01.2008	_	Part Number 10ns Version Adding					
		P1	Features Access time 10ns and operating current 115mA adding					
		P2	Order Information Type No R1RW0408DGE-0PRAdding					
			DC Characteristics Operating power supply current 10ns parameter adding					
		P7	AC Characteristics Read ,Write parameter 10ns parameter adding					
		P8/P9						

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